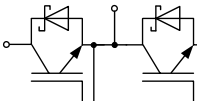


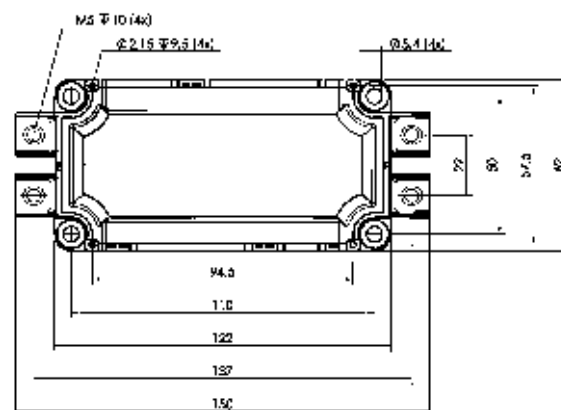
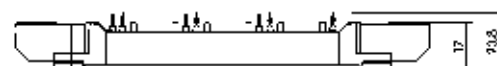
SiC Modules / Hybrid SiC / SEMiX

Type	IGBT						Diode			Module		
	$I_c @ T_c = 25^{\circ}C$	Current (A)	$V_{CE(sat)} @ T_j = 25^{\circ}C \text{ typ.}$	E_{on}	E_{off}	$R_{th(j-c)}$	$I_f @ T_c = 25^{\circ}C$	V_f	$R_{th(j-c)}$	Case	$R_{th(l-c-s)}$	Circuit
	A	A	V	mJ	mJ	K/W	A	V	K/W		K/W	
1200V - IGBT4 (Trench)												
SEMiX603GB12E4SiCp	1110	600	1.80	17	72	0.037	404	1.40	0.14	3p	0.012	

Footnotes: 1) Sample status

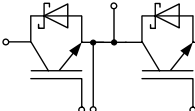
Cases

SEMIX 3p



Dimensions in mm

SiC Modules / Hybrid SiC / SEMITRANS

Type	IGBT						Diode			Module		
	$I_c @ T_c = 25^{\circ}C$	Current (A)	$V_{CE(sat)} @ T_j = 25^{\circ}C \text{ typ.}$	E_{on}	E_{off}	$R_{th(j-c)}$	$I_F @ T_c = 25^{\circ}C$	V_F	$R_{th(j-c)}$	Case	$R_{th(c-a)}$	Circuit
	A	A	V	mJ	mJ	K/W	A	V	K/W		K/W	
1200V - IGBT4 (Trench)												
SKM200GB12T4SiC2 ¹⁾	313	200	1.80	7	20	0.14	246	1.40	0.21	3	0.038	

1200V - IGBT4 (Fast Tr

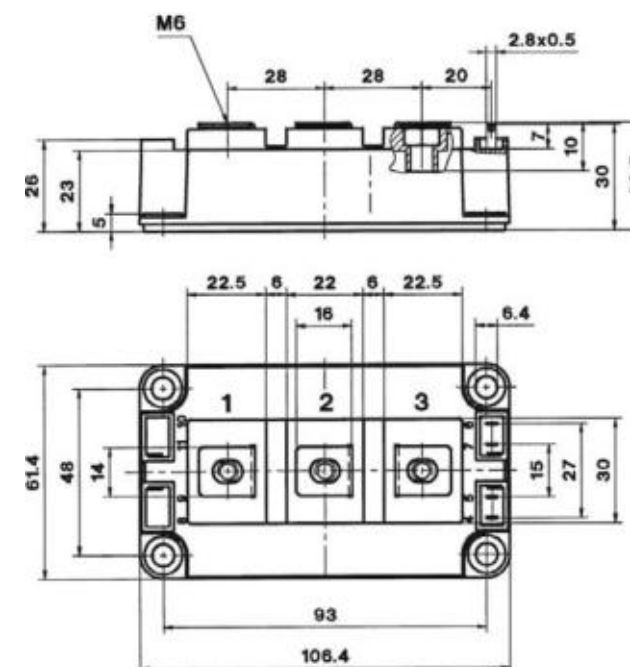
1200V - IGBT4 (Fast Trench)

SKM200GB12F4SiC²⁾	279	200	2.06	7	17	0.14	246	1.40	0.21	3	0.038
SKM200GB12F4SiC³⁾	279	200	2.06	7	17	0.14	123	1.40	0.42	3	0.038

Footnotes: 1) Sample status

Cases

SEMITRANS 3



Dimensions in mm